

600V, 30A, Trench FS II Fast IGBT

General Description

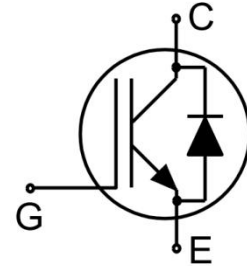
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 600V Trench FS II IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology offering
- Very low $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE30TD60B	TO-220	NCE30TD60B



Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate- Emitter Voltage	± 30	V
I_C	Collector Current	60	A
	Collector Current @ $T_C = 100^\circ\text{C}$	30	A
I_{Cpuls}	Pulsed Collector Current, t_p limited by T_{jmax}	120	A
-	turn off safe operating area, $V_{CE}=600\text{V}$, $T_j=175^\circ\text{C}$	120	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	30	A
I_{FM}	Diode Maximum Forward Current	120	A
P_D	Power Dissipation @ $T_C = 25^\circ\text{C}$	230	W
	Power Dissipation @ $T_C = 100^\circ\text{C}$	115	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	260	$^\circ\text{C}$
t_{sc}	Short circuit withstand time $V_{GE}=15\text{V}$, $V_{CC}\leq 400\text{V}$, Allowed number of short circuits<1000Time between short circuits: $\geq 1.0\text{s}$, $T_j\leq 150^\circ\text{C}$	5	us

Thermal Characteristic

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	0.65	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for Diode	0.99	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Value			Units	
			Min.	Typ.	Max.		
Static Characteristics							
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0\text{V}, I_{CE}=1\text{mA}$	600	--	--	V	
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}, V_{CE}=600\text{V}$	--	--	40	μA	
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30\text{V}, V_{CE}=0\text{V}$	--	--	200	nA	
$I_{GES(R)}$	Gate to Emitter Reverse Leakage	$V_{GE}=-30\text{V}, V_{CE}=0\text{V}$	--	--	200	nA	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=30\text{A}$	--	$T_J=25^{\circ}\text{C}$	1.7	1.9	V
		$V_{GE}=15\text{V}$		$T_J=175^{\circ}\text{C}$	1.9	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=1\text{mA}, V_{CE}=V_{GE}$	4.0	5.0	6.0	V	
Dynamic Characteristics							
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$	--	3552	--	pF	
C_{oes}	Output Capacitance		--	106	--		
C_{res}	Reverse Transfer Capacitance		--	67	--		
Q_g	Total Gate Charge	$V_{CC}=480\text{V}, I_C=30\text{A}, V_{GE}=15\text{V}$	--	132	--	nC	
Q_{ge}	Gate to Emitter Charge		--	28	--		
Q_{gc}	Gate to Collector Charge		--	54	--		
$I_{C(SC)}$	Short circuit collector current Max.1000 short circuits Time between short circuits: $\geq 1.0\text{s}$	$V_{GE}=15\text{V}, V_{CC}\leq 400\text{V}, t_{SC}\leq 5\mu\text{s}, T_J\leq 150^{\circ}\text{C}$	--	180	--	A	
Switching Characteristics							
$t_{d(ON)}$	Turn-on Delay Time	$V_{CC}=400\text{V}, I_C=30\text{A}, V_{GE}=0/15\text{V}, R_g=5\Omega,$ Inductive Load	--	19	--	ns	
t_r	Rise Time		--	17	--		
$t_{d(OFF)}$	Turn-Off Delay Time		--	166	--		
t_f	Fall Time		--	16	--		
E_{on}	Turn-On Switching Loss		--	0.36	--	mJ	
E_{off}	Turn-Off Switching Loss		--	0.32	--		
E_{is}	Total Switching Loss		--	0.68	--		

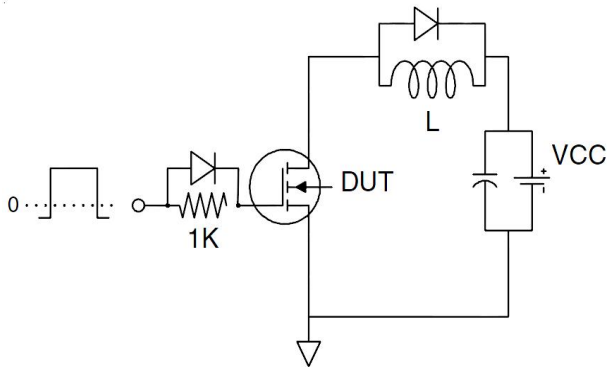
Electrical Characteristics of the Diode ($T_c=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{FM}	Diode Forward Voltage	$I_F=30\text{A}$	--	1.75	2.40	V
T_{rr}	Reverse Recovery Time	$I_F=30\text{A}, di/dt=200\text{A}/\mu\text{s}$	--	178	--	ns
I_{RRM}	Diode Peak Reverse Recovery Current		--	4	--	A
Q_{rr}	Reverse Recovery Charge		--	0.4	--	μC

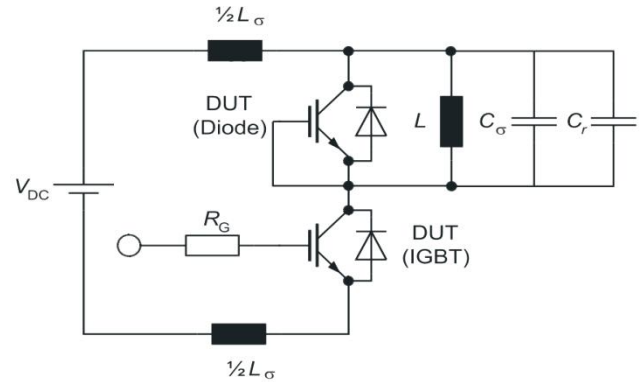
Pulse width $t_p\leq 380\mu\text{s}, \delta\leq 2\%$

Test Circuit

1) Gate Charge Test Circuit

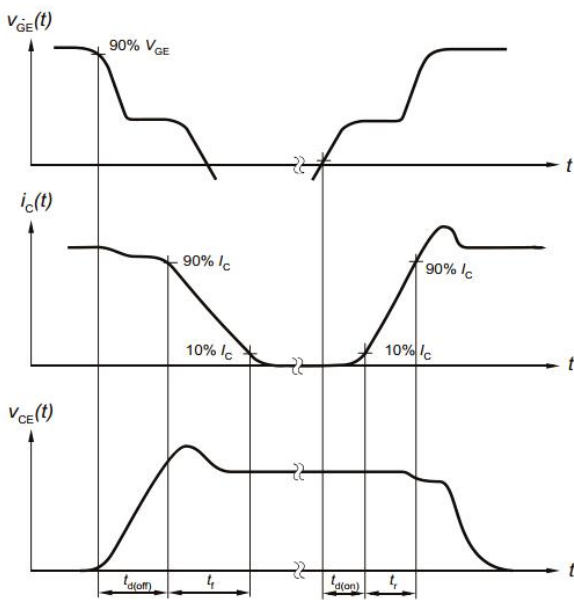


2) Switch Time Test Circuit

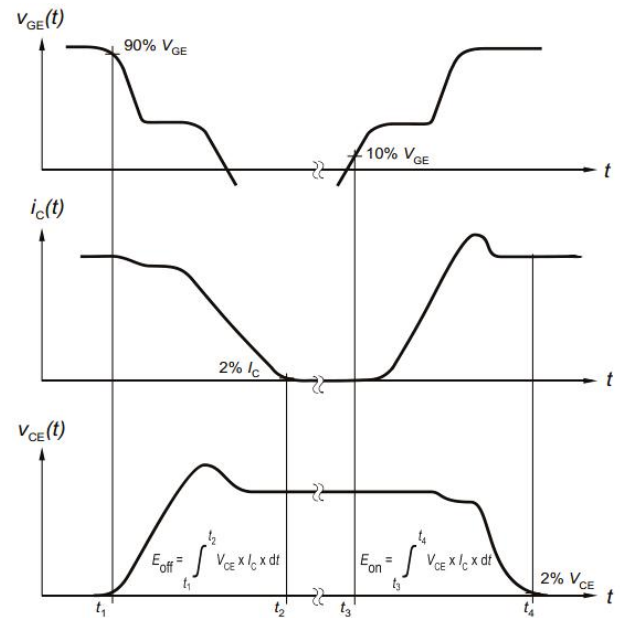


Switching characteristics

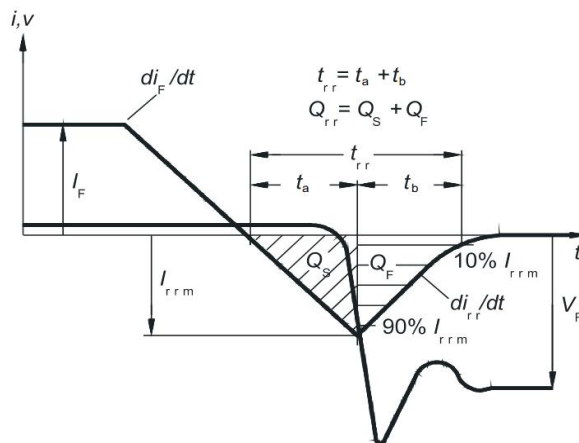
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

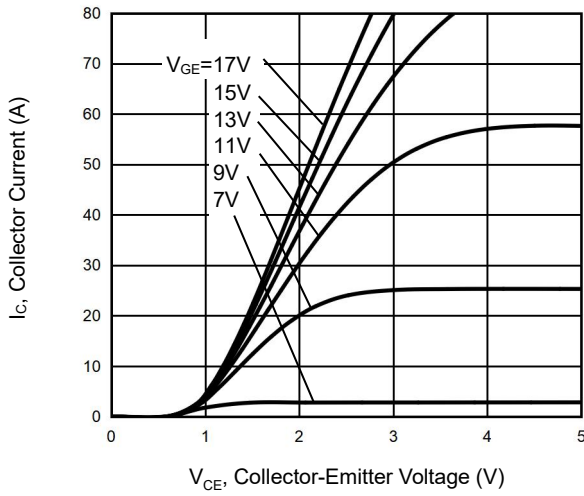


Figure 2 Transfer Characteristics

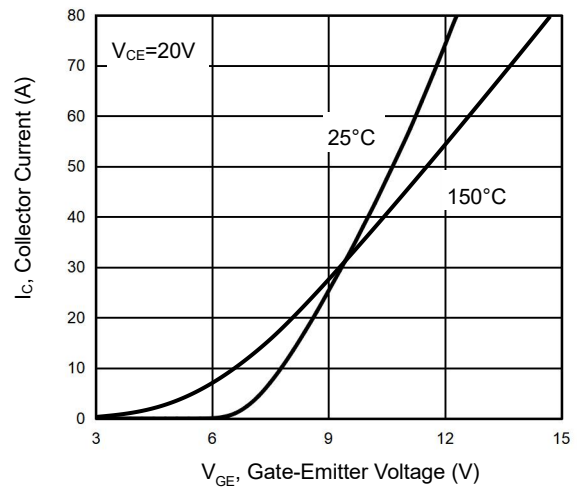


Figure 3 V_{CEsat} vs. Case Temperature

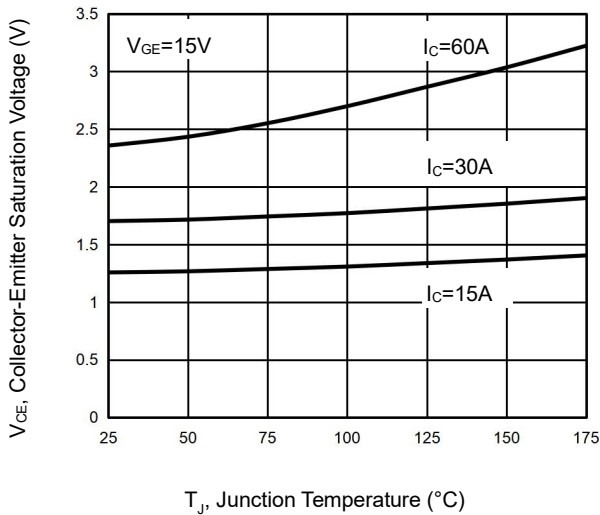


Figure 4 Saturation Voltage vs. V_{GE}

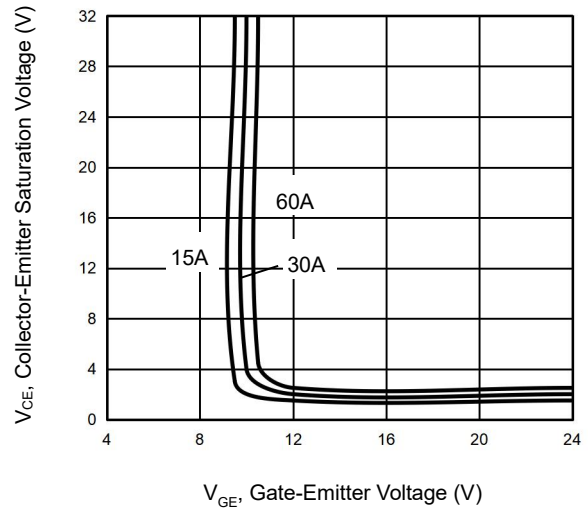


Figure 5 Capacitance Characteristics

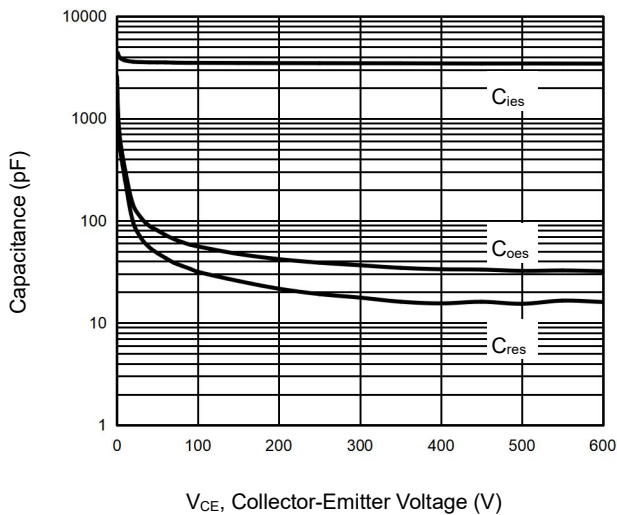
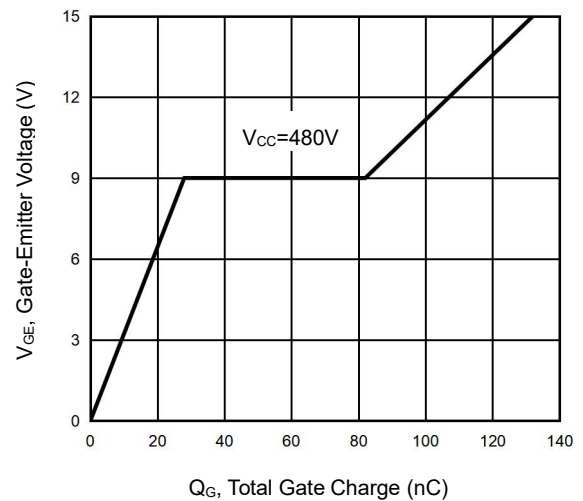


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics

Figure 7 Gate-emitter Threshold Voltage as a Function of Junction Temperature

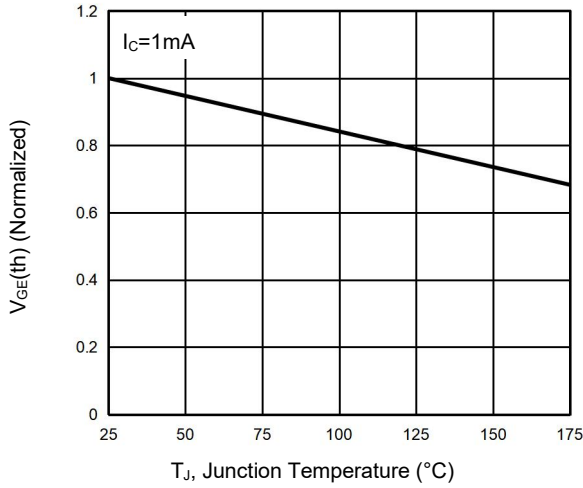


Figure 8 Power Dissipation as a Function of Case Temperature

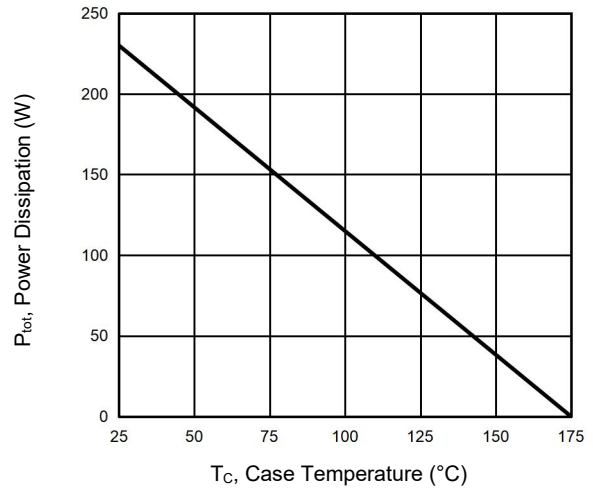


Figure 9 Typical Switching Times as a Function of Gate Resistor

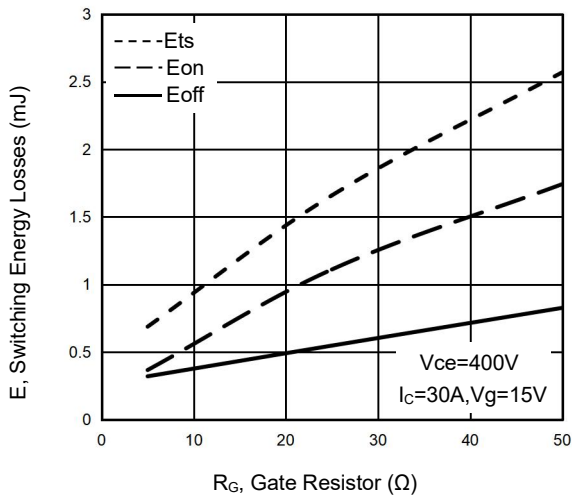


Figure 10 Typical Switching Times as a Function of Junction Temperature

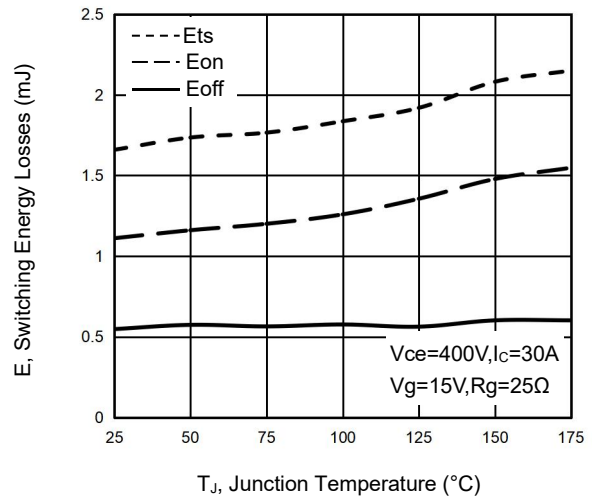


Figure 11 Typical Collector-emitter Saturation Voltage as a function of Collector Current

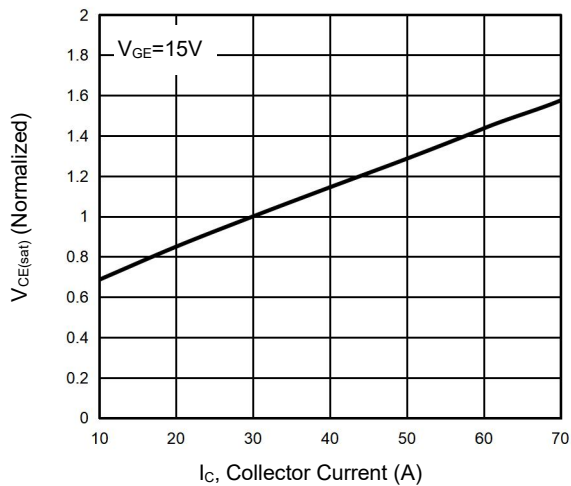
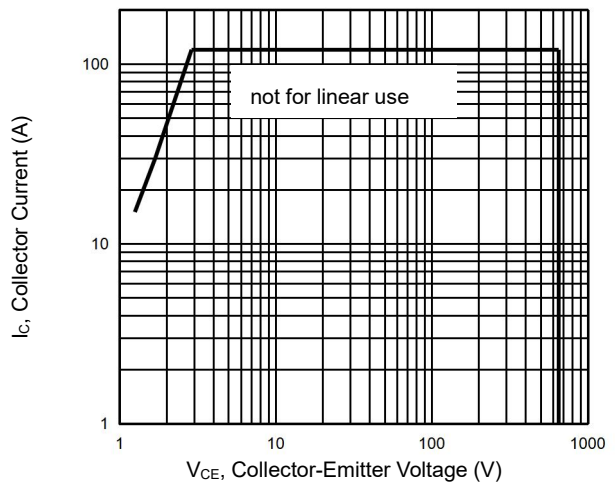


Figure 12 Forward Bias Safe Operating Area



Typical Electrical and Thermal Characteristics

Figure 13 IGBT Transient Thermal Impedance

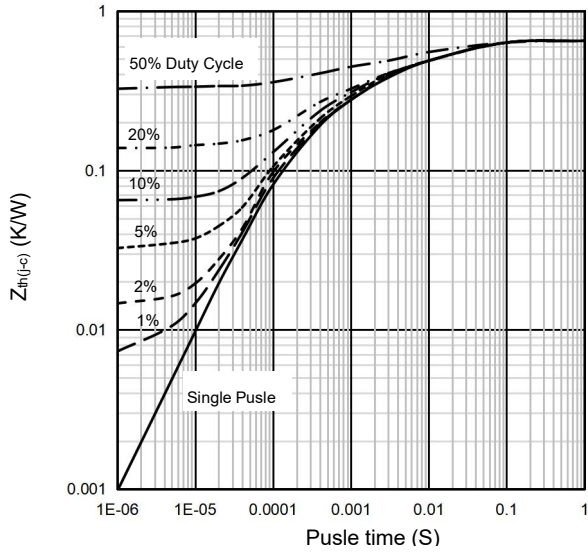
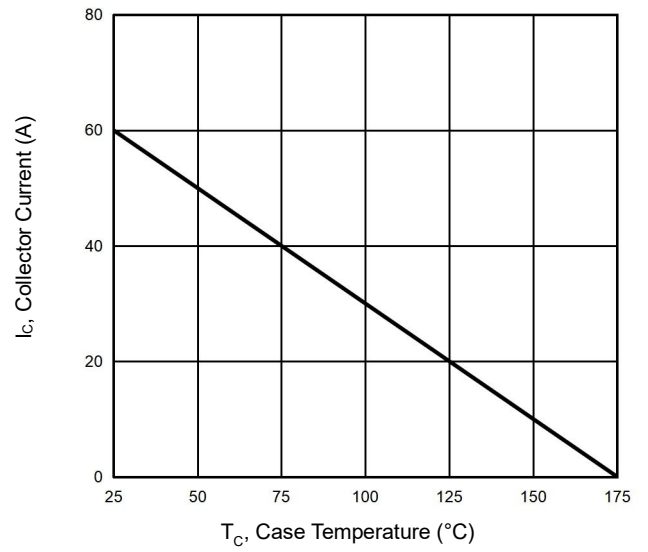
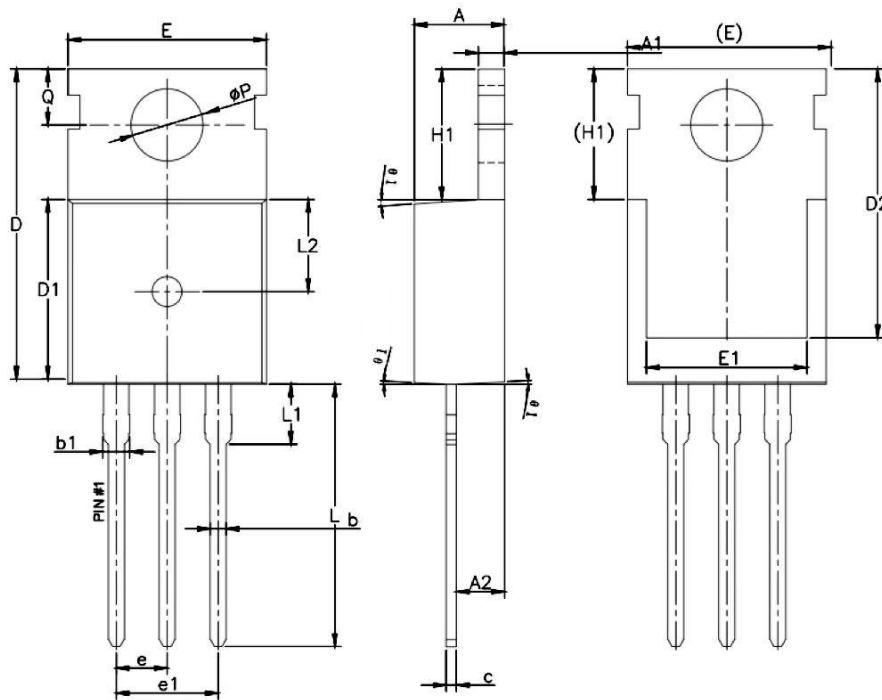


Figure 14 I_c vs. Temperature



TO-220-P Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.17	0.18
A1	1.27	1.33	0.05	0.05
A2	2.30	2.50	0.09	0.10
b	0.70	0.90	0.03	0.04
b1	--	1.40	--	0.06
c	0.45	0.60	0.01	0.02
D	15.30	16.10	0.60	0.63
D1	9.10	9.30	0.36	0.37
D2	13.10	13.70	0.52	0.54
E	9.70	10.20	0.38	0.40
E1	7.80	8.20	0.31	0.32
e	2.54BSC		0.10BSC	
e1	5.08BSC		0.20BSC	
H1	6.30	6.70	0.25	0.26
L	12.78	13.38	0.50	0.53
L1	--	3.50	--	0.14
L2	4.60REF		0.18REF	
ΦP	3.55	3.65	0.13	0.14
Q	2.73	2.87	0.10	0.11
Θ1	1°	5°	0.04	0.20

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